

DTW

March 8, 2006



To: Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, NY 12603

Subject:

Serial No. 10/661,038 09/12/03

Cheng T. Horng et al.

PROCESS AND STRUCTURE TO
FABRICATE SPIN VALVE HEADS FOR
ULTRA-HIGH RECORDING DENSITY
APPLICATION

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation In An Application.


The following Patents and/or Publications are submitted to comply with the duty
of disclosure under CFR 1.97-1.99 and 37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States
Postal Service as first class mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on March 9, 2006.

Stephen B. Ackerman, Reg. # 37761

Signature/Date

 3/9/06

40% Tunneling Magnetoresistance After Anneal at 380 Degrees C for Tunnel Junctions with Iron-Oxide Interface Layers,” by Shang et al., Journal of Applied Physics, Vol. 89, No. 11, June 1, 2001, pp. 6665-6667, discloses thermal stability for MTJs being improved up to 380 degrees C by the insertion of an iron-oxide layer with appropriate thickness between the AlOx barrier and the CoFe pinned electrode.

Oxygen as a Surfactant in the Growth of Giant Magnetoresistance Spin Valves,” by W. F. Egelhoff, Jr., et al. Journal of Applied Physics, Vol. 82, No. 12, December 15, 1997, pp. 6142-6151, discusses a novel method for increasing the giant magnetoresistance (GMR) of Co/Cu spin valves with the use of oxygen.

Sincerely,

A handwritten signature in black ink, appearing to be 'SBA', written over a horizontal line.

Stephen B. Ackerman,
Reg. No. 37761

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION
13 2006
(Use several sheets if necessary)

HT-03-006

10/661,038

Cheng T. Horng et al.

09/12/03

Group 1 Unit

[illegible][illegible]

- "40% Tunneling Magnetoresistance After Anneal at 380°C for Tunnel Junctions with Iron-Oxide Interface Layers," by Shang et al., *Jrnl. of Appl. Physics*, Vol. 89, No. 11, June 1, 2001, pp. 6665-6667.
- "Oxygen as a Surfactant in the Growth of Giant Magnetoresistance Spin Valves," by W.F. Egelhoff, Jr. et al., *Jrnl. of Appl. Physics*, Vol. 82, No. 12, Dec. 15, 1997, pp. 6142-6151.

ΟΛΤΕ ~~CON~~DELEO

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.